

Electron localization in sound absorption oscillations in the quantum Hall effect regime

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The absorption coefficient for surface acoustic waves in a piezoelectric insulator in contact with a GaAs/AlGaAs heterostructure (with two-dimensional electron mobility $\mu = 1.3 \times 10^5 \text{ cm}^2/\text{V} \cdot \text{s}$) at $T=4.2\text{K}$) via a small gap has been investigated experimentally as a function of the frequency of the wave, the width of the vacuum gap, the magnetic field, and the temperature. The magnetic field and frequency dependencies of the high-frequency conductivity (in the region 30-210 MHz) are calculated and analyzed. The experimental results can be explained if it assumed that there exists a fluctuation potential in which current carrier localization occurs. The absorption of the surface acoustic waves in an interaction with two-dimensional electrons localized in the energy "tails" of Landau levels is discussed.

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I. INTRODUCTION

The problems of quantum interference of electrons, i.e., weak localization in a two-dimensional electron gas (2DEG), just as problems of strong charge-carrier localization (associated with defects of the crystal lattice), occupy a central place in two-dimensional nanoelectronics, but they have still not been adequately investigated. The characteristic features of localization in a 2DEG can be studied by investigating rf conductivity of a 2DEG in the quantum Hall effect regime [1]

One proven method for investigating rf conductivity is the acoustic method, which makes it possible to measure the rf conductivity of semiconductors without any electrical contacts on the sample. The crux of this method is that a piezoelectrically active sound wave accompanied by an electric field undergoes absorption as a result of interaction with electrons as it propagates in the semiconductor, and this absorption is directly related to the electrical conductivity of the sample.

Acoustic methods have been successfully used to study the rf conductivity of a three-dimensional electron gas in doped compensated semiconductors at low temperatures [2,3]. It has been shown that if the electrons are in a free (delocalized) state, then the ultrasonic absorption coefficient of the electrons in the semiconductor, which is a piezoelectric material, in a magnetic field H is determined completely by its dc conductivity $\sigma_{xx}^{dc}(H)$. If, however, electrons are localized at separate impurity centers or in a random fluctuation potential produced by the impurities, as in the case of a strongly doped and strongly compensated semiconductor, then the conduction mechanisms in a constant electric field and in the rf field accompanying the acoustic wave are different. In the static case the conductivity $\sigma_{xx}^{dc}(H)$ is of a hopping character and the rf conductivity $\sigma_{xx}^{ac}(H)$ can remain "metallic", and in addition $\sigma_{xx}^{dc}(H) \neq \sigma_{xx}^{ac}(H)$. By studying

the ultrasonic absorption coefficient of the electrons as a function of the magnetic field intensity, temperature, ultrasonic frequency, and ultrasonic wave intensity in the three-dimensional case it was possible to determine not only the character of the carrier localization but also the corresponding numerical parameters.

On this basis, it is helpful to extend the acoustic method of investigating rf conductivity to semiconductor structures with a 2DEG. The interaction of surface acoustic waves (SAWs) with two-dimensional electrons was first observed in GaAs/AlGaAs type heterostructures [4,5]. It was shown that the SAW energy is absorbed as a result of this interaction, and the magnitude of the absorption is determined by the conductivity of the 2DEG. For this reason, in a quantizing magnetic field, when Shubnikov-de Haas (SdH) oscillations appear, the absorption coefficient for the surface acoustic wave also oscillates. The oscillations of this coefficient are sharpest in the region of magnetic fields where the quantum Hall effect regime obtains. In this connection, by analogy with the three-dimensional semiconductors, the characteristic features of localization in a 2DEG in a quantum Hall effect regime can be studied by studying the temperature, frequency and magnetic field dependencies of the sound absorption and, which is especially important, this can be done by studying the conductivity measured by a contact-free method.

Two experimental configurations are now employed. In the first one SAWs are excited in the standard manner on the surface of a piezoelectric crystal (for example, LiNbO_3), and the experimental structure with the 2DEG is placed above the surface of a piezodielectric crystal with a gap, whose width is less than the wavelength. In the second configuration the experimental structure itself, which must be a piezoelectric, serves as the sound duct. Surface acoustic waves are excited in it and at the same time the interaction of sound with the 2DEG is

investigated. The first configuration has the advantage that the gap eliminates the deformation interaction of the two-dimensional (2D) electrons with SAWs, and only the interaction with the electric fields produced by the SAWs in the piezoelectric crystal remains. However, this method is inconvenient because it is almost impossible to determine the width of the gap by direct measurements. In experiments employing the second configuration there is no gap at all, but in this case the deformation interaction of the 2D electrons with the SAWs cannot be ignored [6].

The first configuration was used in [4] and the second was used in [5–8]. In all of these investigations it was concluded that the character of the dependence of the SAW absorption coefficient of the two-dimensional electrons on the magnetic field H is determined by the dc conductivity $\sigma_{xx}^{dc}(H)$ and its dependence on H . However, in [9], where the SAW absorption of a 2DEG in a InGaAs/InP heterostructure was measured in the first experimental configuration with $T=4.2$ K, it was shown that this assertion is valid only for high Landau-level numbers and in stronger magnetic fields (i.e., small filling numbers $\nu = nhc/2eH$, where n is the Hall electron density) the variation of the SAW absorption coefficient as a function of H is not determined by $\sigma_{xx}^{dc}(H)$.

In the present work the dependencies of the SAW absorption coefficient Γ of 2D electrons on the magnitude and direction (longitudinal and transverse with respect to the normal to the plane of the 2DEG) of the magnetic field up to $H=60$ kOe, the SAW frequency in the range $f=30$ –210 MHz, and the temperature in the range $T=1.4$ –4.2 K are investigated using the first experimental configuration mentioned above for the purpose of studying the rf conductivity and the character of electron localization in structures of this type in the integral quantum Hall effect regime. To get a better physical picture of the phenomena, galvanomagnetic measurements of the components of the dc resistivity tensor were performed as a function of the magnetic field up to $H=50$ kOe.

II. EXPERIMENTAL PROCEDURE AND RESULTS

The GaAs/AlGaAs structures investigated were prepared by molecular-beam epitaxy. A layer of gallium arsenide with residual impurity density 10^{15} cm^{-3} and thickness of the order of $1 \mu\text{m}$ (the so-called buffer layer) was grown on a semiinsulating GaAs (001) substrate of thickness $d = 300 \mu\text{m}$. Next, a $50\text{-}\text{\AA}$ -thick undoped layer of the solid solution AlGaAs (spacer) and an approximately $500\text{-}\text{\AA}$ -thick layer of a solid solution of the same composition but doped with silicon with an electron density $n = 10^{18} \text{ cm}^{-3}$ were grown. The top (contact) layer of the structure consisted of a $200\text{-}\text{\AA}$ gallium arsenide film doped with silicon [$n \simeq (3 - 4) \times 10^{18} \text{ cm}^{-3}$].

The samples for the dc galvanomagnetic measurements and for measurements by acoustic methods were prepared from neighboring regions of the heterostructure. The measurements were performed with dc current $I = 1020 \mu$ (which ensured that there would be no heating effects) in the temperature range 1.8–4.2 on mesa structures etched out in the form of a double cross with contact pads. We present below the results of our investigations for a structure with Hall density $n = 1.6 \times 10^{11} \text{ cm}^{-2}$ and Hall mobility $\mu = 1.3 \times 10^5 \text{ cm}^2/(\text{V} \cdot \text{s})$ at $T=4.2$ K. The density calculated according to the SdH oscillations was $n_{SH} = 6.8 \times 10^{11} \text{ cm}^{-2}$. The results of the measurements of the components ρ_{xx} and ρ_{xy} of the resistivity tensor as a function of the magnetic field H (in the QHE region) at $T=1.5$ K is presented in Fig. 1.

A piezoelectrically active surface wave, excited on the Y-cut surface of a LiNbO_3 crystal (see inset in Fig. 2) and propagating in the Z direction, was used for the acoustic measurements. The SAW was produced and detected with interdigital transducers with fundamental frequency 30, 90, and 150 MHz. In addition, higher-order harmonics were also used in the experiment. The sample was placed directly on the lithium niobate surface, along which a SAW propagated, and detected with the aid of a spring. The sample was located in a cryoduct in a vacuum chamber. The vacuum gap between the piezoelectric and the sample, determined by the roughness of their surfaces, is designated by the letter a in the diagram shown in the inset in Fig. 2. A longitudinal electric field (along the direction of propagation of the acoustic wave), which arises with the motion of the SAW in the piezoelectric crystal, penetrates into the experimental object, and the 2DEG is then located in an alternating electric field whose frequency equals the frequency of the surface acoustic wave. The interaction of the 2D electrons in the experimental heterostructure with the SAW electric field causes the wave to decay, and this decay is recorded by the transducer employed. The independence of the absorption coefficient Γ from the intensity of the sound wave was checked in the experiment, i.e., the measurements were performed in a regime linear in the electric field.

Figure 2 shows the dependence of the absorption coefficient for a SAW with frequency $f=30$ MHz on the intensity of a magnetic field, oriented in a direction normal to the surface of the heterostructure, at $T=4.2$ K and for different vacuum gap widths a . Similar curves were also obtained for other frequencies and temperatures. An interesting feature is observed on the curves in Fig. 2: In strong magnetic fields the maxima of the absorption Γ split and the lower the temperature, the lower the magnetic field intensity at which splitting is observed. The maxima of Γ are equally spaced as function of $1/H$ and for large Landau numbers they correspond, with respect to the magnetic field, to the minima of $\sigma_{xx}^{dc}(H)$; for higher fields H , when σ_{xx}^{dc} becomes small at the minima of the

oscillations ($< 10^{-7}\Omega^{-1}$) the absorption maxima split in two and the conductivity minimum (and also the center of the Hall plateau) corresponds to an absorption minimum.

We also measured the absorption of SAWs in a magnetic field oriented parallel to the surface of the sample. In this geometry the SAW absorption oscillations were not observed. This confirms the two-dimensional character of the absorption oscillations which we observed in a transverse magnetic field.

An interesting feature of the absorption of SAWs in strong magnetic fields is the inequality, observed for small filling numbers, in the amplitudes of the SAW absorption maxima in the presence of splitting. In [5] this fact was attributed to the inhomogeneity of the experimental samples. We performed a very large number of measurements on several GaAs/AlGaAs differently positioned (with different vacuum gaps) samples, and we observed both a different asymmetry of the peaks and the same height of the peaks on the same sample; this is illustrated in Fig. 2. It is not yet clear what causes this effect.

III. ANALYSIS OF THE EXPERIMENTAL DATA

The equal spacing of the peaks in the dependence of the absorption of surface acoustic waves (SAWs) on the quantity $1/H$ makes it possible to determine the density of 2DEG from the period of the oscillations by the standard method. The density obtained in this manner equals, within the limits of accuracy of the experiment, the density n calculated according to the SdH oscillations.

The absorption coefficient Γ , which is associated with the interaction of a SAW with two-dimensional electrons, in the experimental configuration employed in our work was calculated in Ref. 10, taking into account the diffusion of current carriers. If the absorption coefficient Γ is introduced as $A = A_0 \exp(-\Gamma x)$, where A_0 and A are the signal amplitudes at the entrance and exit, respectively, and x is the length of the sample, then Γ is (in cm^{-1})

$$\Gamma = \chi^{(1)} k \frac{\pi \sigma f_2(k)/\varepsilon_s v}{1 + [Dk/v + 2\pi \sigma f_1(k)/\varepsilon_s v]^2}. \quad (1)$$

In [10] $\chi^{(1)} \simeq K^2$ is the electromechanical coupling constant of LiNbO_3 ; k and v are, respectively, the SAW wave vector and velocity; D is the diffusion coefficient; ε_s is the permittivity of the semiconductor; and σ is the conductivity of the 2DEG. We shall estimate the contribution of diffusion to the absorption coefficient without expanding the functions f_1 and f_2 (expressions for which are presented in [10]). For a degenerate 2DEG the diffusion coefficient is

$$D = \sigma \hbar^2 / e^2 m^* = \pi \sigma a_B / \varepsilon_s, \quad (2)$$

where m^* is the electron effective mass, and a_B is the effective Bohr radius (for electrons in GaAs $a_B \simeq 100\text{\AA}$). We note that for all frequencies and vacuum gap widths employed in the experiment, the value of f_1 calculated according to Eq. (10) from [10] ranged from 0.6 to 1.4, so that the two terms in the denominator of (1) satisfy the relation

$$D \frac{k}{v} \ll \frac{2\pi \sigma}{v \varepsilon_s} f_1 \quad (3)$$

(which reduces to the inequality $k \ll 2f_1/a_B$), and it is natural to use below the formula for the absorption coefficient neglecting the diffusion term. If expression (1) is rewritten in the "symmetric" form, setting σ equal to σ_{xx} - the conductivity of a 2DEG in a magnetic field and assuming the distance from the channel with the 2DEG to the surface of the sample equals 0 (which corresponds to the experimental structure), then Γ in dB/cm is given by

$$\Gamma = 34.72b(k, a)(\varepsilon_1 + \varepsilon_0)\varepsilon_s^2 e^{(-2ka)} \times \\ \times K^2 k \frac{(\frac{4\pi\sigma_{xx}}{\varepsilon_s v})r(k, a)}{1 + [(\frac{4\pi\sigma_{xx}}{\varepsilon_s v})r(k, a)]^2}, \quad (4)$$

where $\varepsilon=51$ ([10]), $\varepsilon=12$, and $\varepsilon_0=1$ are the permittivities of LiNbO_3 , GaAs, and of the vacuum gap between the sample and LiNbO_3 respectively;

$$b(k, a) = [c - te^{(-2ka)}][c + m - te^{(-2ka)} - pe^{(-2ka)}]^{-1},$$

$$r(k, a) = \frac{c + m - te^{(-2ka)} - pe^{(-2ka)}}{2[c - te^{(-2ka)}]},$$

where $c = (\varepsilon_1 + \varepsilon_0)(\varepsilon_s + \varepsilon_0)$, $t = (\varepsilon_1 - \varepsilon_0)(\varepsilon_s \varepsilon_0)$, $m = (\varepsilon_1 + \varepsilon_0)(\varepsilon_s - \varepsilon_0)$, and $p = (\varepsilon_1 - \varepsilon_0)(\varepsilon_s + \varepsilon_0)$.

Let us now analyze Γ as a function of σ_{xx} in accordance with (4). If the conductivity is high, then

$$(4\pi\sigma_{xx}/v\varepsilon_s)r(k, a) \gg 1 \quad (5)$$

and $\Gamma \sim \sigma_{xx}$; if (for low conductivity)

$$(4\pi\sigma_{xx}/v\varepsilon_s)r(k, a) \ll 1 \quad (6)$$

then the absorption coefficient $\Gamma \sim \sigma_{xx}$. Therefore, it is obvious that for

$$(4\pi\sigma_{xx}/v\varepsilon_s)r(k, a) = 1 \quad (7)$$

the function $\Gamma(H)$ possesses a maximum Γ_M , and from (4) and (7) it is obvious that the value of Γ_M does not depend on the value of σ_{xx} . The equality (7) in our case corresponds to

$$\sigma_{xx} r(k, a) = v$$

since $4\pi/\varepsilon_s \simeq 1$ for GaAs. Let us now consider the dependence of the maximum absorption coefficient Γ_M on the wave frequency f , which follows from 4 and which is shown in Fig. 3 for different values of a . It is obvious from Fig. 3 that the dependence $\Gamma_M(f)$ has a maximum, and the width of the vacuum gap increases with decreasing value of Γ_M , so that the maximum occurs at a lower frequency.

If we now refer to Fig. 2, then on the basis of the fore-going analysis of 4 it is possible to explain the splitting of the maxima of Γ at low filling numbers. Indeed, near the conductivity maxima, where $\sigma_{xx} \simeq 10^{-5}\Omega^{-1}$ the condition 5 is satisfied and the absorption coefficient Γ assumes its minimum values. As the magnetic field increases, within the same Landau level the quantity σ_{xx} starts to decrease rapidly, and the coefficient Γ in accordance with 5 increases, until σ_{xx} decreases to a value corresponding to condition (7). In this case $\Gamma(H)$ reaches its maximum value Γ_M . As σ_{xx} decreases further, the condition (6) is satisfied and the coefficient Γ , correspondingly, also decreases. This occurs right up to values of H for which $\sigma_{xx}(H)$ reaches its minimum value. As the magnetic field increases further, σ_{xx} again increases, the changes in Γ occur in the reverse order. As a result, a second maximum appears in the dependence $\Gamma()$. In weaker magnetic fields the quantity $\sigma_{xx}(H)$ does not reach at the minima the values for which the equality (7) holds. For this reason, splitting of the maxima of $\Gamma()$ does not occur. As the temperature decreases, the oscillations of $\sigma_{xx}(H)$ become sharper and deeper, which is reflected in the corresponding curves for $\Gamma(H)$ as a splitting of the maxima with the larger numbers.

To calculate from Γ the dissipative conductivity σ_{xx} , it is necessary to know the gap width a between the insulator and the experimental object. In our case the heterostructure is pressed directly to the lithium niobate surface and a is a poorly controllable parameter, since it is determined by irregularities of unknown amplitude on both surfaces. The effective value of a can be determined from acoustic measurements by investigating the frequency dependence of the maximum value of the absorption coefficient Γ . For the same placement of the sample, i.e., for the same value of a but different SAW frequencies, we obtain [see Eqs (4) and (7)]

$$\frac{\Gamma(k_1)}{\Gamma(k_2)} = \frac{[k_1 b(a, k_1)]}{[k_2 b(a, k_2)]} e^{-2a(k_1 - k_2)}. \quad (8)$$

The value of a determined from this equation was found to be $0.25 - 1\mu m$ for different placements of the sample. Knowing a , it is possible to determine from relation (4) and the experimentally measured values of Γ the conductivity σ_{xx}^{ac} and its dependence on the magnetic field. It was found that this quantity, which was determined from the acoustic measurements for different values of a in the range of magnetic fields corresponding

to absorption coefficient minima (conductivity maxima), corresponds within 20% to the values of σ_{xx}^{dc} (for the same values of H) which were calculated from the galvanomagnetic measurements of the dependences $\rho_{xx}(H)$ and $\rho_{xy}(H)$ in a direct current:

$$\sigma_{xx}^{dc}(H) = \frac{\rho_{xx}(H)}{[\rho_{xy}(H)]^2 + [\rho_{xx}(H)]^2}. \quad (9)$$

This equality apparently means (by analogy with the three-dimensional case) that in the indicated range of magnetic fields the static conductivity σ_{xx}^{dc} is determined by carriers in delocalized states.

To analyze further the experimental SAW absorption curves we employed the vacuum gap a as a parameter, choosing it so that near the conductivity maxima σ_{xx}^{ac} would equal σ_{xx}^{dc} . In this method of determination, the vacuum gap a differs by no more than 20% from the gap calculated from (8).

IV. DISCUSSION

Figure 4 shows the magnetic field dependencies of the dissipative conductivity $\sigma_{xx}^{ac}(H)$, which were obtained from the SAW absorption coefficient for different frequencies and gap widths a , as well as the dependence $\sigma_{xx}^{dc}(H)$ near the maximum with filling number $\nu = nhc/2eH=3.5$, where n is the Hall electron density. It should be noted that if the value of a determined by the method described in the preceding section is substituted into (4) and the value of σ_{xx}^{dc} measured in a direct current is used for σ_{xx} , then it is not possible to describe the entire experimental dependence $\Gamma(H)$.

It is obvious from Fig. 4 that the conductivities are equal to each other in magnetic fields in the range 37-45 kOe, but as the magnetic field moves away from the maximum in different directions, they separate, and σ_{xx}^{ac} is always greater than σ_{xx}^{dc} . In our view, the difference of the rf and static conductivities describes the transition through the mobility threshold from free to localized electronic states and correspondingly to different mechanisms of conduction in static and rf electric fields.

To explain the experimental data on SAW absorption, we assume that the Landau levels are smeared in space by the fluctuation potential which may not be small. Indeed, in the best GaAs/AlGaAs-type structures the mobility of the 2DEG at $T=4.2K$ reaches values of $\mu \simeq 10^7 cm^2/(V \cdot s)$, i.e., it is two orders of magnitude greater than the mobility in the structure investigated by us. The simplest explanation for the difference in σ_{xx}^{ac} and σ_{xx}^{dc} could be as follows: Far from the maxima the conductivity σ_{xx} is of the character of hops along localized states and should therefore increase with frequency f as $\sigma \sim f^s (s = 1)$ [1]. However, as we shall show below, this is at variance with the experimental conclusion that

in measurements of Γ at different frequencies and calculations of σ_{xx}^{ac} from them we did not observe a frequency dependence of σ_{xx}^{ac} within the limits of the experimental error, i.e., according to our data $\sigma = 0$. Therefore, a more adequate model is the model of a large-scale fluctuation potential and the assumption that for 2DEG a "mobility threshold" exists in our samples. As a result, in the range of magnetic fields where the Fermi level lies above the mobility threshold (region of maximum σ_{xx}), the electrons are delocalized and $\sigma_{xx}^{ac}(H) = \sigma_{xx}^{dc}(H)$. As the magnetic field varies, the Fermi level crosses the mobility threshold, causing a percolation-type transition, in which the electrons are localized in the random potential, forming so-called "lakes" with metallic-type conductivity. In the latter case the static conductivity mechanism becomes different from the rf conductivity mechanism: The static conductivity is determined by the activation transfer of electrons to the percolation level and the rf conductivity, whose magnitude is larger than that of the static conductivity, is determined by the conductivity in the lakes (along closed orbits for free 2D electrons, determined by the relief formed by fluctuations of the potential energy). This model is supported by the fact that in the range of magnetic fields where $\sigma_{xx}^{ac}(H) = \sigma_{xx}^{dc}(H)$ the quantity ρ_{xy} increases abruptly at a transition between two quantum plateaus (Fig. 4), which corresponds to the position of the Fermi level in the region of delocalized states [11].

It is very difficult to calculate the SAW absorption coefficient of 2D electrons localized in a random potential. For this reason, we assume, by analogy with the three-dimensional case [3] that for the two-dimensional conductivity the formula for Γ , which describes SAW absorption in this case, will have the same structure as (4), but a factor Σ , which depends on the magnetic field and temperature, appears in this case in front of the fraction. For a three-dimensional electron gas, the physical meaning of the coefficient $\Sigma(H)$ is that of a relative volume occupied by the conducting "drops," whereas in our case (2DEG) $\Sigma(H)$ is approximately proportional to the density of electrons which are localized on the minima of the fluctuation potential (lakes) and which realize in the lakes a conduction in the electric field of the SAW. As a result,

$$\Gamma = \Sigma(H)\Gamma(\sigma_{xx}^l), \quad (10)$$

where $\Gamma(\sigma_{xx}^l)$ corresponds to expression (4) with σ_{xx} replaced by σ_{xx}^l the conductivity in the lakes. In the range of fields H where the electrons are delocalized, the function $\Sigma(H) = 1$ and

$$\sigma_{xx}^{ac}(H) = \sigma_{xx}^{ac}(H),$$

and then the value of Σ becomes less than 1. Therefore, to calculate $\sigma_{xx}^{ac}(H)$ in the entire range of magnetic fields,

it is necessary to know the value of Σ and its magnetic-field dependence.

The following operation was performed to determine $\Sigma(H)$: The ratio of the experimentally measured values of $\Gamma(H)$ and $\Gamma(H)$ was determined near each maximum of σ_{xx} with respect to the magnetic field in the range of magnetic fields where $\Gamma \sim l/\sigma$, assuming that near the percolation level $\sigma_{xx}^{ac} = \sigma_{xx}^{ac}$. Then

$$\frac{\Gamma(H)}{\Gamma(H_{max})} = \frac{\Sigma(H)\sigma_{xx}^{dc}(H_{max})}{\sigma_{xx}^{dc}(H)}. \quad (11)$$

since $\Gamma(H)$ is determined according to (4). As indicated above, the ratio $\sigma_{xx}^{dc}(H_{max})/\sigma_{xx}^{dc}(H)$ is calculated from the components $\rho_{xx}(H)$ and $\rho_{xy}(H)$ of the resistivity tensor which are measured for this sample.

Another method to obtain Σ was to determine it from the quantity Γ_M (see Fig. 2). This method did not require a knowledge of σ_{xx}^{ac} , since we obtain from Eqs. (4), (7), and (10) the expression

$$\Gamma = \Sigma(H)17.36K^2 \exp(-2ka)(\varepsilon_1 + \varepsilon_0)\varepsilon_s \varepsilon_0^2 b(k, a). \quad (12)$$

The dependence of the function Σ , which is determined by the methods described above, on $|\Delta\nu|$ at $T=4.2$ in the magnetic field range corresponding to filling numbers ν from 3 to 4, where $\Delta\nu$ is measured from $\nu=3.5$, is shown in Fig. 5. It should be noted that the points on the plot were obtained from the values of the absorption coefficient for different SAW frequencies and different values of a . The value of Σ depends on the temperature and is a subject of our further investigations. The solid line in Fig. 5 was estimated by eye and extrapolated to the region $\Delta\nu=0.5$, so that it was impossible to calculate the value of Σ near the conductivity minima because of the lack of accurate data on the value of the static conductivity in the limit $\sigma_{xx}^{dc} \rightarrow 0$.

Knowing the vacuum gap and the function $\Sigma(H)$, the value of $\Sigma(H)$ could be determined according to Eqs. (4) and (10) from the experimental values of Γ . The results of such calculations are presented in Fig. 6 for $T=4.2$. The different points correspond to curves obtained at different frequencies and with different vacuum gaps. The solid line represents the function $\sigma_{xx}^{dc}(H)$. As one can see from Fig. 6, for large Landau numbers $\sigma_{xx}^{ac}(H) = \sigma_{xx}^{dc}(H)$, just as in the weaker magnetic fields, but only near the conductivity maxima. In the regions of the magnetic field where $\sigma_{xx}^{dc} \rightarrow 0$, however, the values of σ_{xx}^{dc} and σ_{xx}^{ac} diverge, and σ_{xx}^{ac} is always greater than σ_{xx}^{dc} , as should be the case on the basis of the model proposed above. The equality $\sigma_{xx}^{ac}(H) = \sigma_{xx}^{dc}(H)$ for high Landau-level numbers is attributable to the fact that the mobility thresholds at $T=4.2$ K for neighboring levels are smeared in energy and overlap, so that the condition for carrier localization is not achieved in weak magnetic fields, even when the chemical potential falls between the Landau levels.

Since σ_{xx}^{ac} is calculated from Γ after a rather complicated procedure of analysis of the experimental data, we

estimate the error in σ_{xx}^{ac} to be of the order of 40%. To this accuracy, the quantity σ_{xx}^{ac} at the minima with respect to the magnetic field for small filling numbers, i.e., in localized states, does not depend on the sound frequency (and in our experiments the frequency varied by a factor of 7).

It should be noted that our results are at variance with the data of [12], where σ_{xx}^{ac} was studied in the Corbino disk geometry in the frequency range 50-600 MHz. The authors found that σ_{xx}^{ac} does not equal to σ_{xx}^{dc} either at the maxima or at the minima of the oscillations of $\sigma_{xx}(H)$ when the filling numbers ν are small. They explained the observed frequency dependence of σ_{xx} in terms of the theory given in [13].

V. CONCLUSIONS

The magnetic field and frequency dependencies of the high-frequency conductivity of the 2DEG in the heterostructure GaAs/AlGaAs (in the region 30-210 MHz) were calculated and analyzed. It was shown that the experimental results can be explained if it is assumed that there exists a fluctuation potential in which carrier localization occurs. The character of the SAW absorption in the presence of an interaction with localized carriers is discussed.

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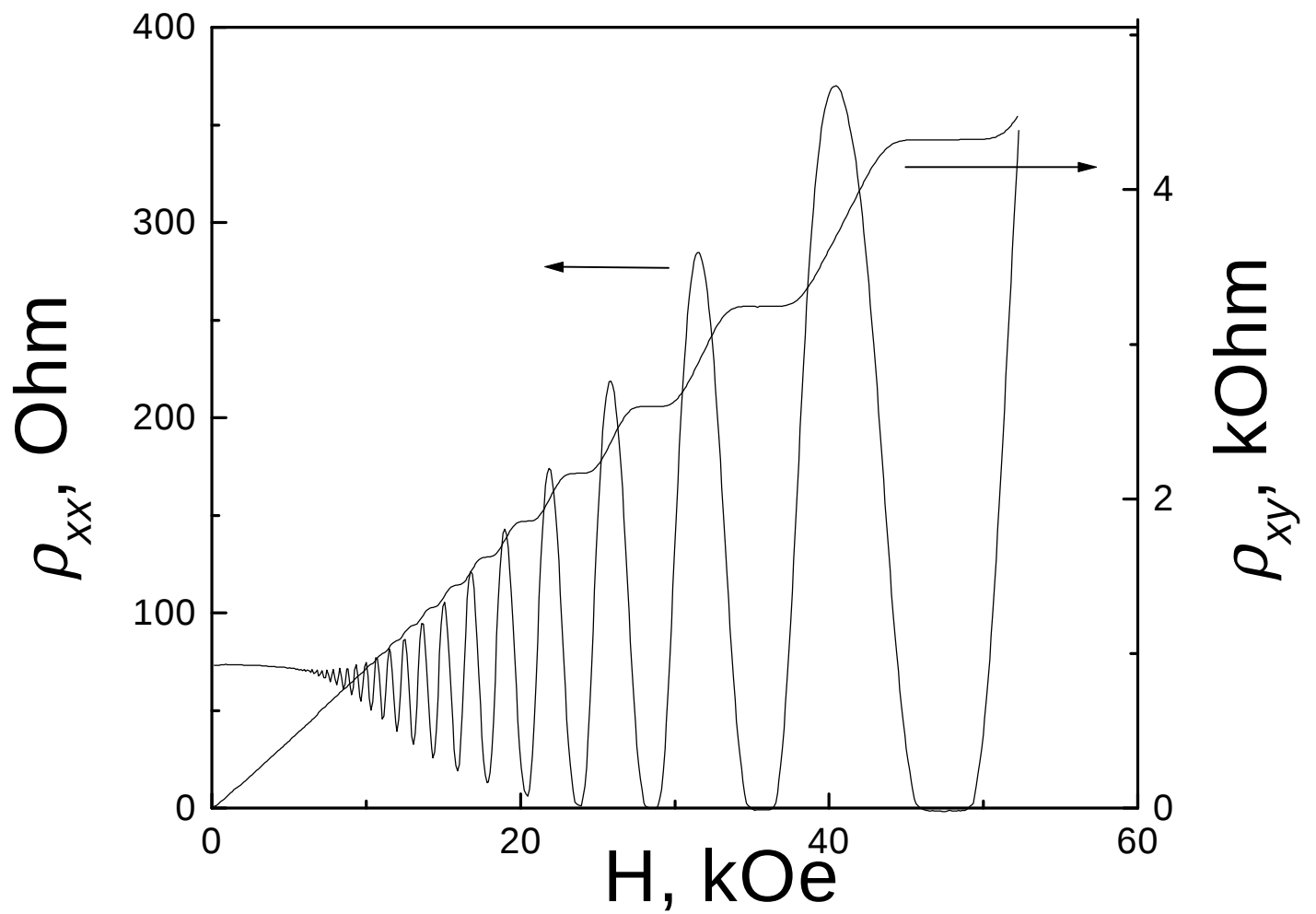


FIG. 1. Resistivity tensor components ρ_{xx} and ρ_{xy} versus the magnetic field H in a GaAs/AlGaAs heterostructure at $T=1.5\text{K}$.

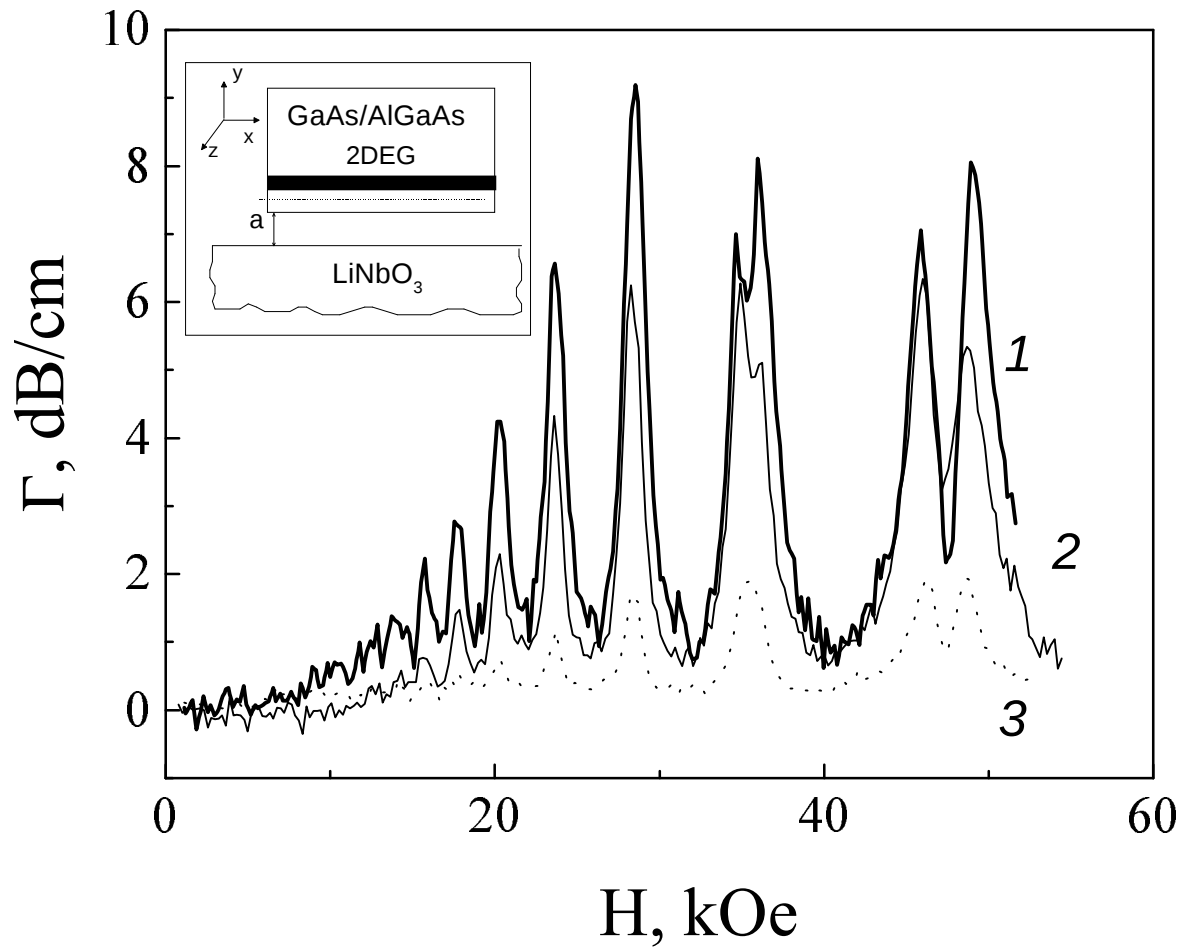


FIG. 2. Surface acoustic wave absorption coefficient Γ versus the magnetic field intensity H at $f=30\text{MHz}$ with vacuum gap widths a , μm : 1 - 0.3, 2 - 0.5, and 3 - 1.0. Inset: Arrangement of the sample with respect to the crystal axes of lithium niobate.

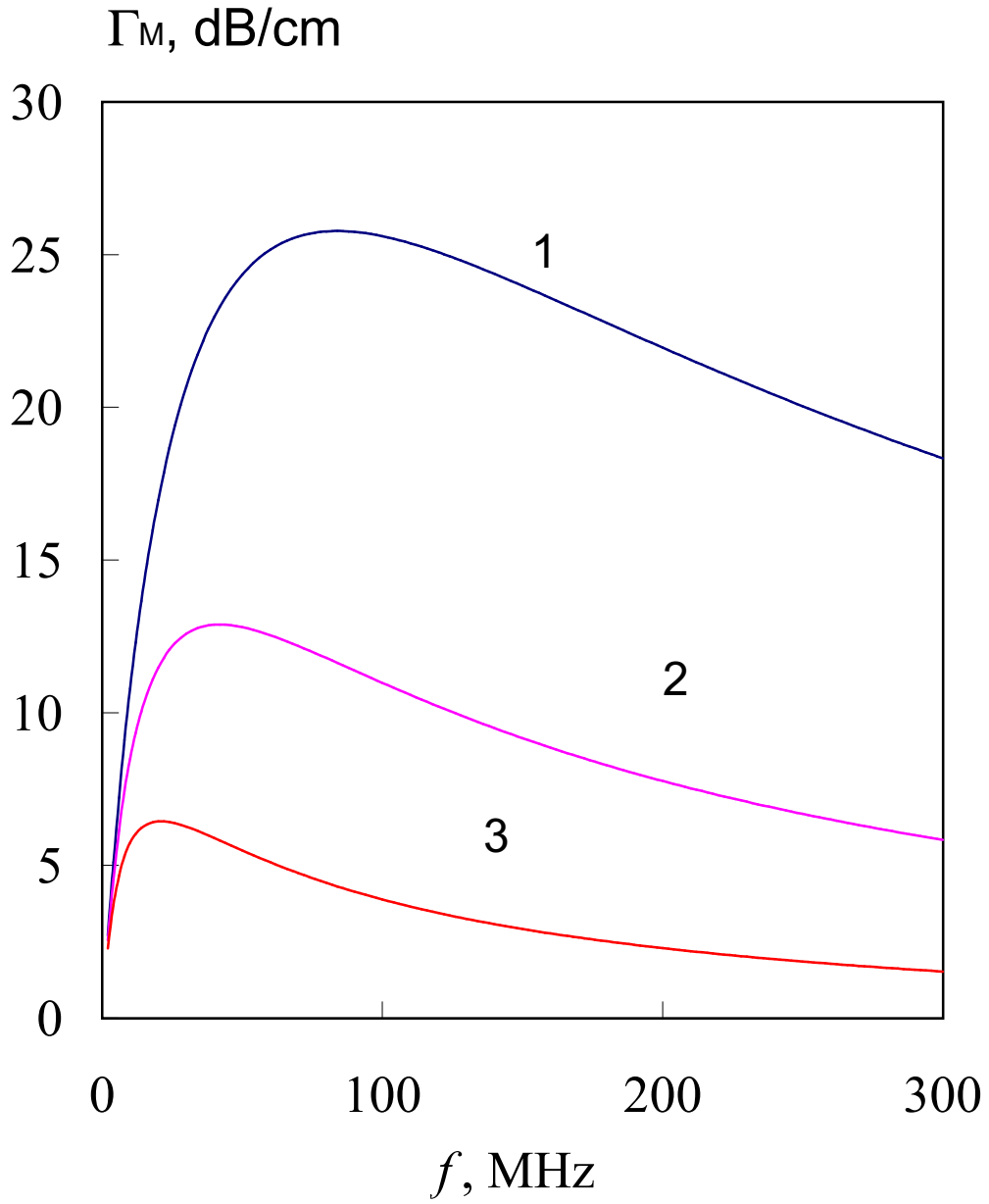


FIG. 3. Theoretical value of the maximum absorption Γ versus acoustic wave frequency f for different vacuum gap widths a , μm : 1 - 0.3, 2 - 0.6, 3 - 1.2.

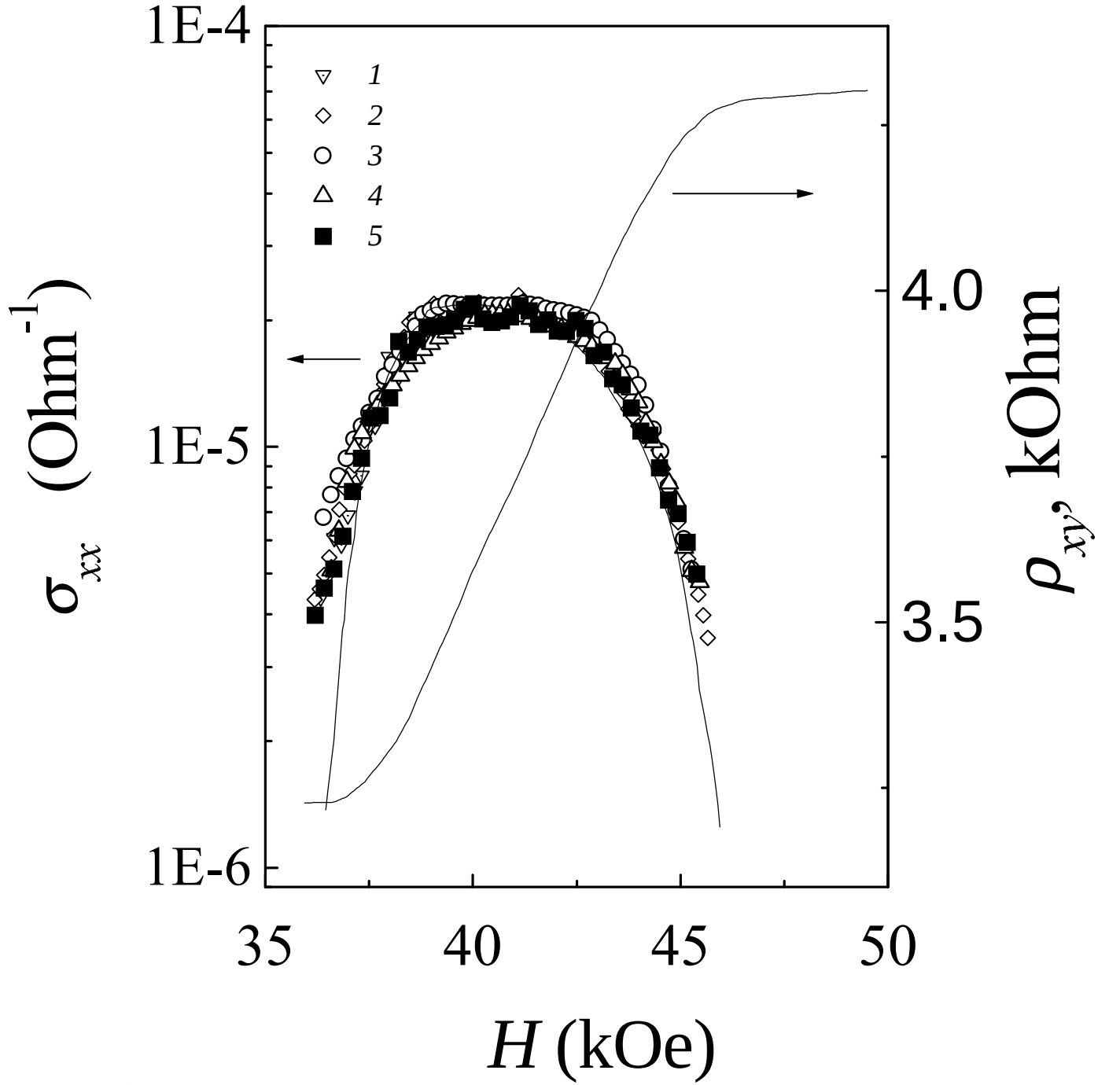


FIG. 4. σ_{xx}^{dc} (solid line) and σ_{xx}^{ac} (symbols) (1) versus the magnetic field H near the region of delocalized states: $\rho_{xy}(H)$. The symbols correspond to frequencies f (MHz) and vacuum gap widths a (in μm): 3 - 213 and 0.3, 4 - 30 and 0.5, 5 - 150 and 0.3, 6 - 30 and 0.4, 7 - 90 and 1.2.

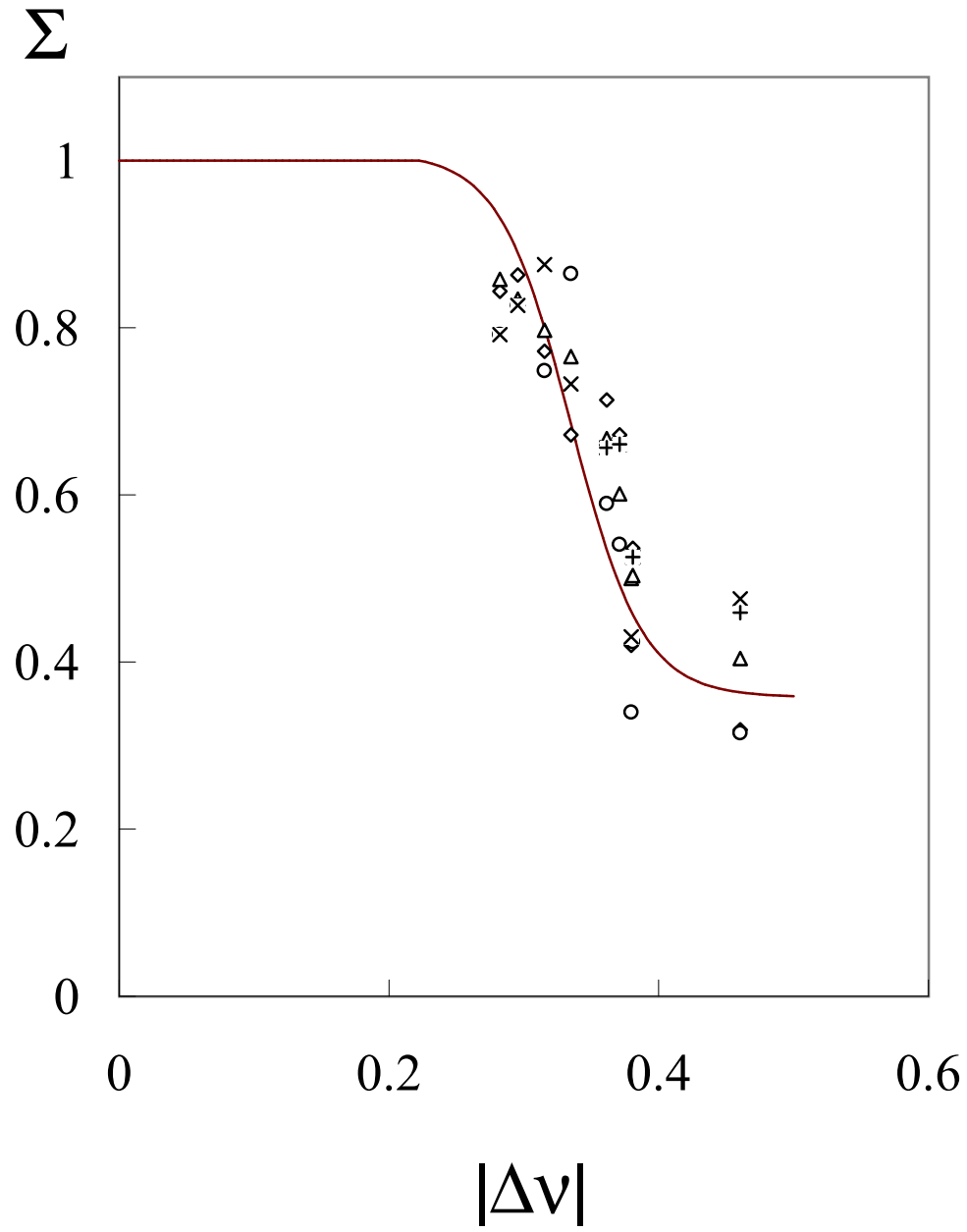


FIG. 5. Σ versus $|\Delta\nu|$ - absolute value of the change in the filling factor ν , measured from $\nu=3.5$. The symbols correspond to frequencies f (MHz) and vacuum gap widths a (in μm): 1 - 213 and 0.3, 2 - 30 and 0.5, 3 - 50 and 0.3, 4 - 30 and 0.4, 5 - 90 and 1.2.

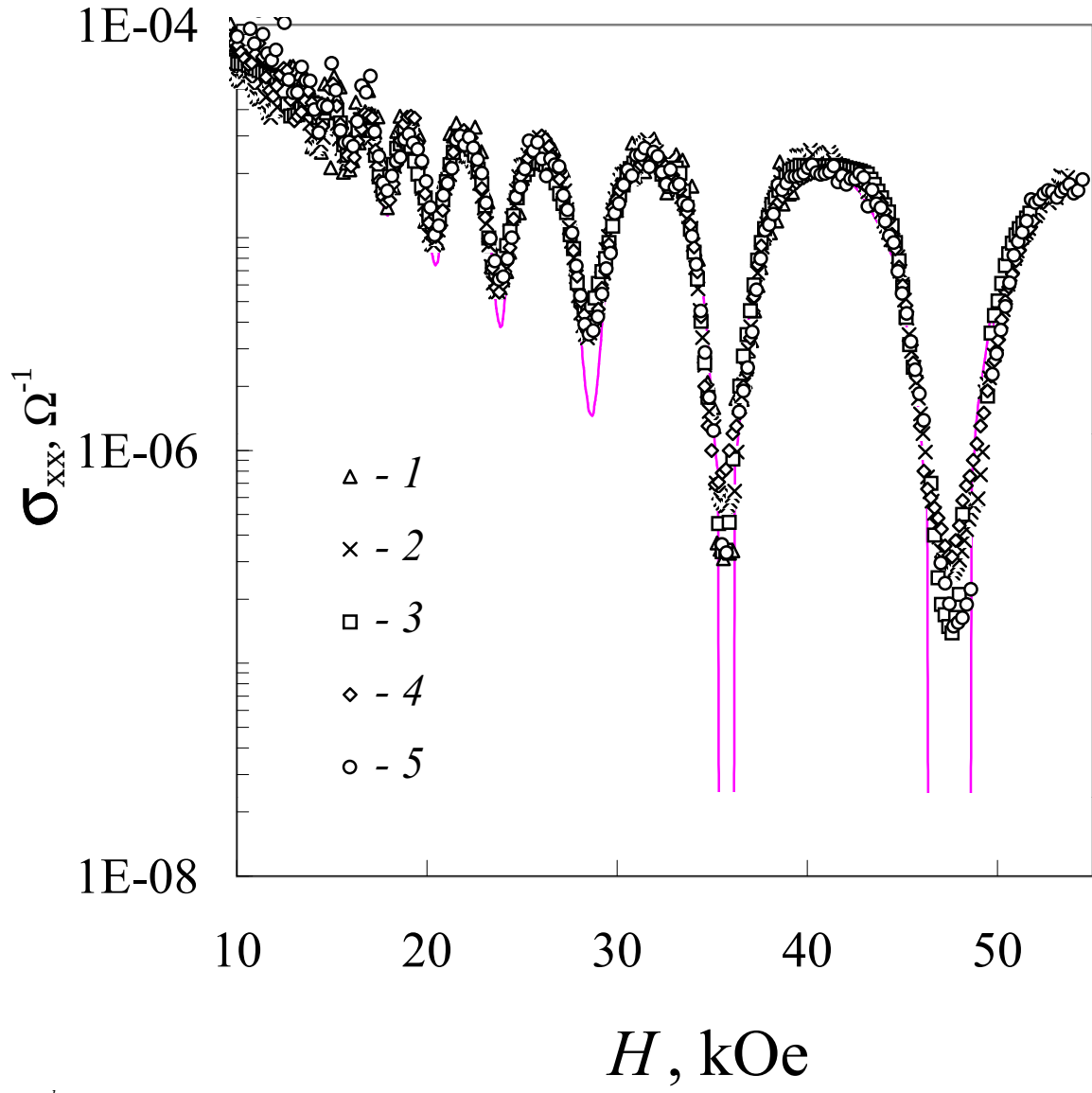


FIG. 6. σ_{xx}^{dc} (solid line) and σ_{xx}^{ac} (symbols) versus the magnetic field H . The different symbols have the same meaning as in Fig. 5.